

# DATA SHEET



## **BYD67** Ripple blocking diode

Product specification  
Supersedes data of 1999 Oct 20

2003 Mar 14

## Ripple blocking diode

BYD67

## FEATURES

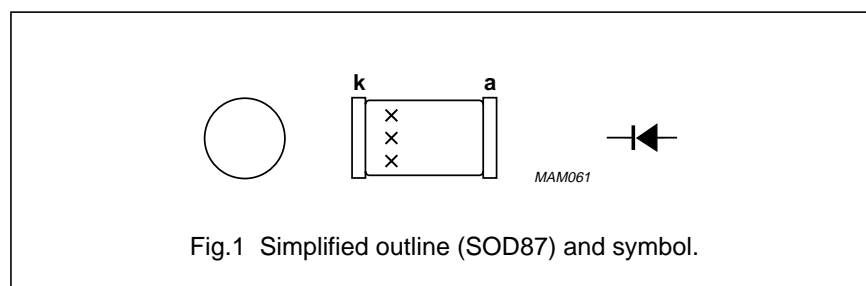
- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier package.

## DESCRIPTION

Cavity free cylindrical glass SOD87 package through Implotec™(1) technology.

(1) Implotec is a trademark of Philips.

The SOD87 is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL      | PARAMETER                           | CONDITIONS   | MIN. | MAX. | UNIT |
|-------------|-------------------------------------|--|------|------|------|
| $V_{RRM}$   | repetitive peak reverse voltage     |  | –    | 300  | V    |
| $V_R$       | continuous reverse voltage          |  | –    | 300  | V    |
| $I_{F(AV)}$ | average forward current             | $T_{tp} = 85\text{ °C}$ ; see Fig.2; averaged over any 20 ms period; see also Fig.4                            | –    | 1.2  | A    |
|             |                                     | $T_{amb} = 60\text{ °C}$ ; PCB mounting (see Fig.8); see Fig.3; averaged over any 20 ms period; see also Fig.4 | –    | 0.4  | A    |
| $I_{FRM}$   | repetitive peak forward current     | $T_{tp} = 85\text{ °C}$  | –    | 11   | A    |
|             |                                     | $T_{amb} = 60\text{ °C}$   | –    | 3.7  | A    |
| $I_{FSM}$   | non-repetitive peak forward current | $t = 10\text{ ms}$ half sine wave; $T_j = 25\text{ °C}$ prior to surge; $V_R = V_{RRMmax}$                     | –    | 5    | A    |
| $T_{stg}$   | storage temperature                 |  | –65  | +175 | °C   |
| $T_j$       | junction temperature                |  | –65  | +175 | °C   |

## Ripple blocking diode

BYD67

**ELECTRICAL CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise specified.

| SYMBOL   | PARAMETER             | CONDITIONS   | MIN. | TYP. | MAX. | UNIT          |
|----------|-----------------------|--|------|------|------|---------------|
| $V_F$    | forward voltage       | $I_F = 1\text{ A}$ ; $T_j = T_{j\text{ max}}$ ; see Fig.5  | –    | –    | 1.7  | V             |
|          |                       | $I_F = 1\text{ A}$ ; see Fig.5   | –    | –    | 2.3  | V             |
| $I_R$    | reverse current       | $V_R = V_{RRM\text{ max}}$ ; see Fig.6   | –    | –    | 1    | $\mu\text{A}$ |
|          |                       | $V_R = V_{RRM\text{ max}}$ ; $T_j = 165\text{ °C}$ ; see Fig.6   | –    | –    | 100  | $\mu\text{A}$ |
| $t_{fr}$ | forward recovery time | when switched to $I_F = 1\text{ A}$ in 50 ns; see Fig.9  | –    | –    | 350  | ns            |
| $t_{on}$ | turn-on time          | when switched from $V_F = 0$ to $V_F = 3\text{ V}$ ; measured between 10% and 90% of $I_{F\text{ max}}$ ; see Fig.10 | 500  | –    | –    | ns            |
| $t_{rr}$ | reverse recovery time | when switched from $I_F = 0.5\text{ A}$ to $I_R = 1\text{ A}$ ; measured at $I_R = 0.25\text{ A}$ ; see Fig.11       | –    | –    | 150  | ns            |
| $C_d$    | diode capacitance     | $f = 1\text{ MHz}$ ; $V_R = 0$ ; see Fig.7   | –    | 17   | –    | pF            |

**THERMAL CHARACTERISTICS**

| SYMBOL                | PARAMETER                                     | CONDITIONS | VALUE | UNIT |
|-----------------------|---|------------|-------|------|
| $R_{th\ j\text{-tp}}$ | thermal resistance from junction to tie-point |            | 30    | K/W  |
| $R_{th\ j\text{-a}}$  | thermal resistance from junction to ambient   | note 1     | 150   | K/W  |

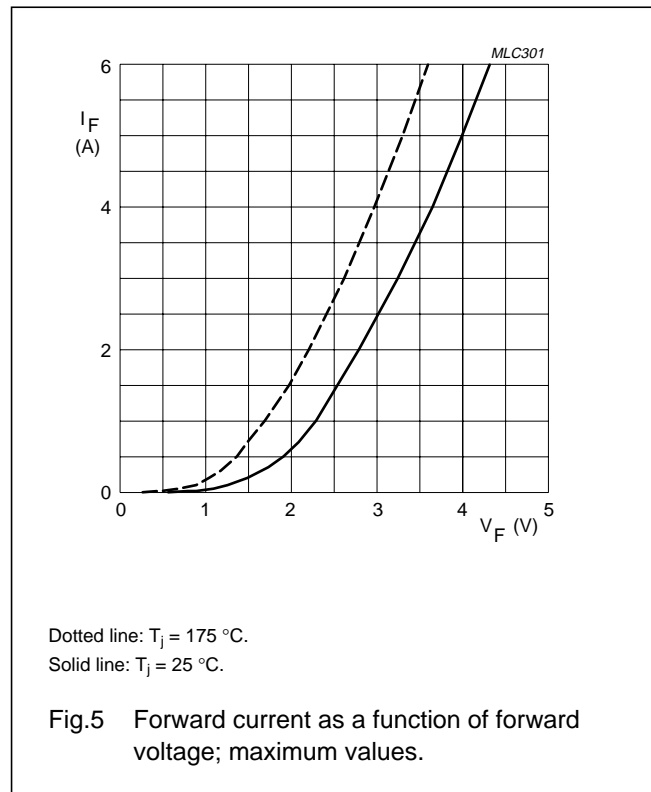
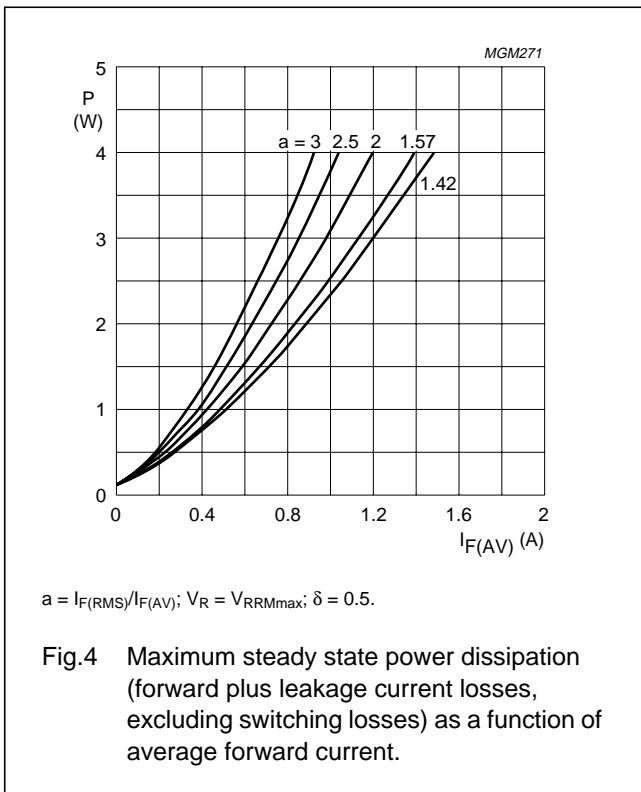
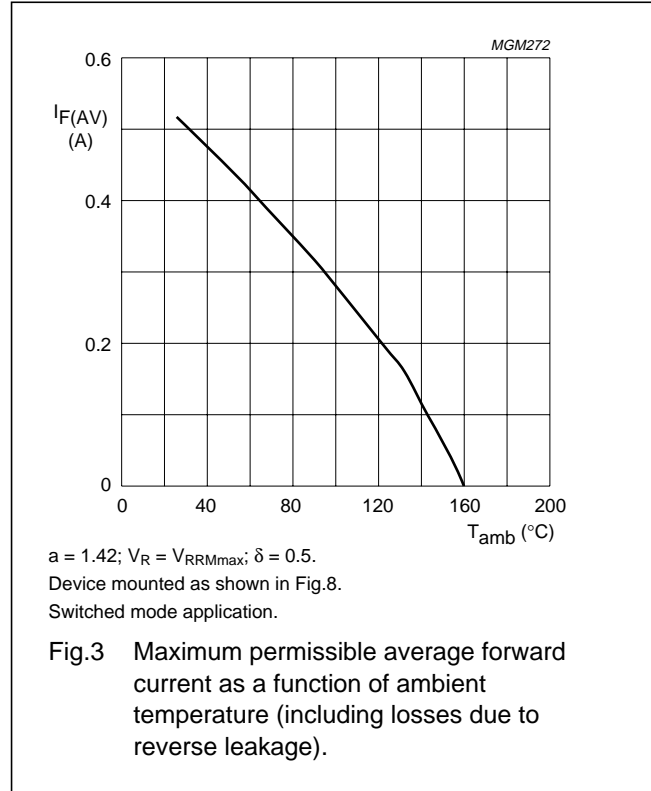
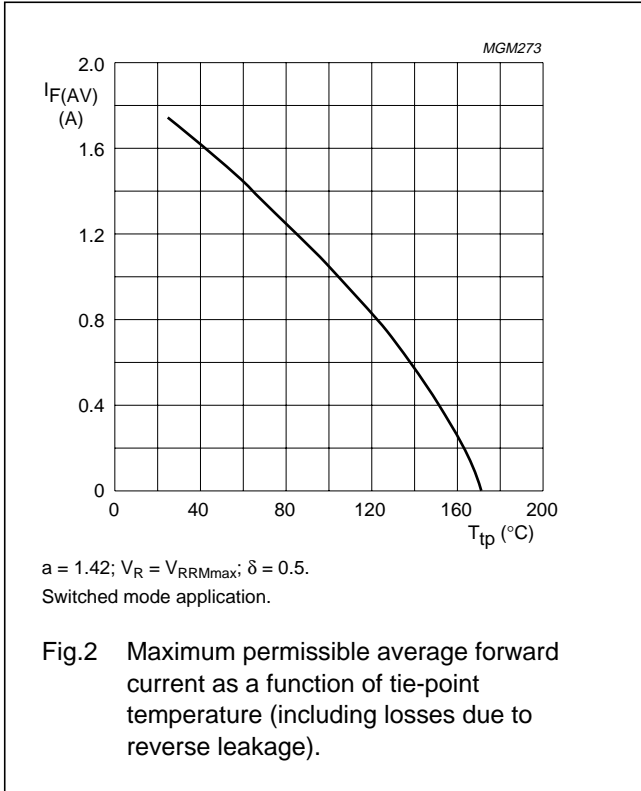
**Note**

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer  $\geq 40\text{ }\mu\text{m}$ , see Fig.8. For more information please refer to the 'General Part of associated Handbook'.

Ripple blocking diode

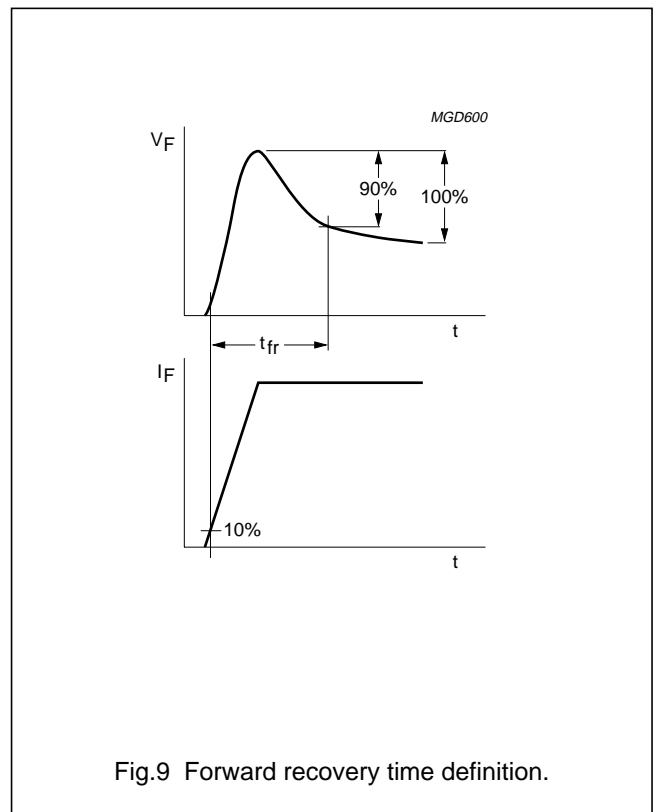
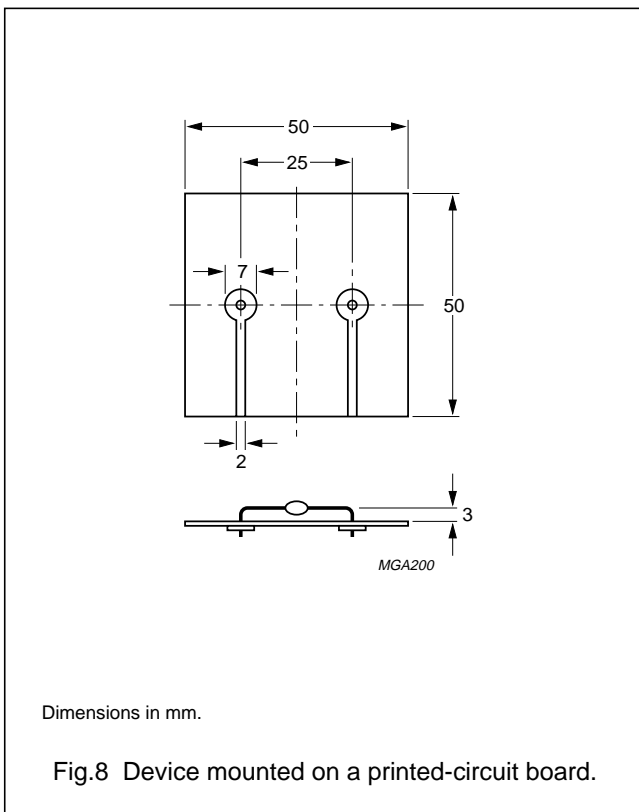
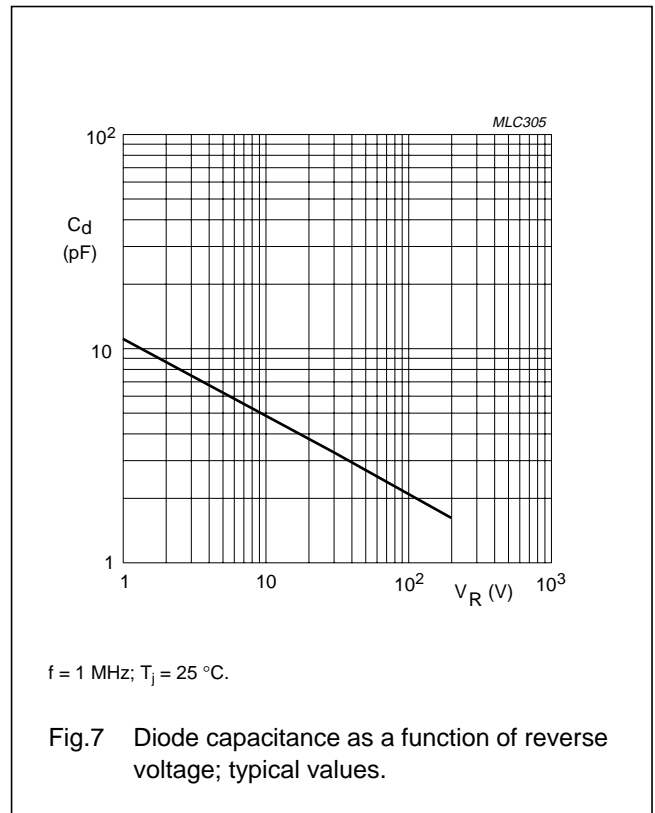
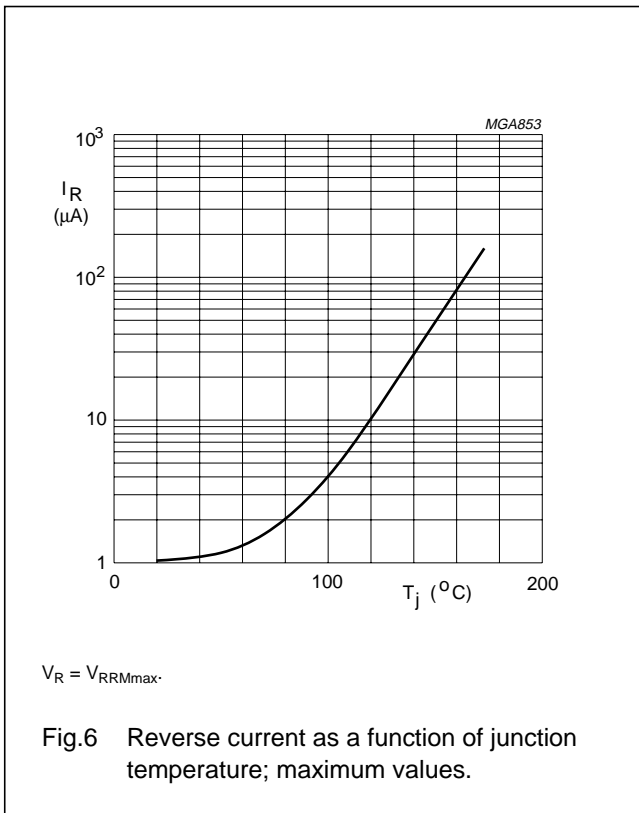
BYD67

GRAPHICAL DATA



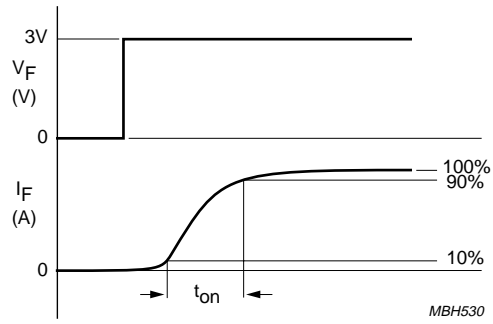
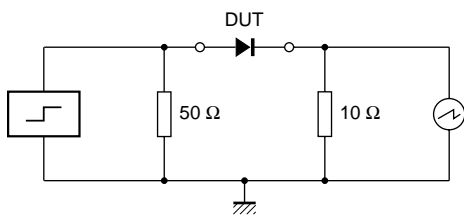
Ripple blocking diode

BYD67



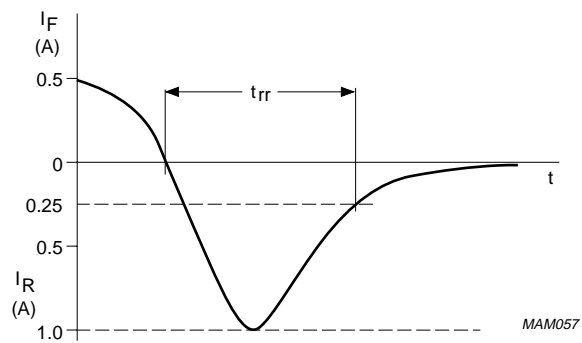
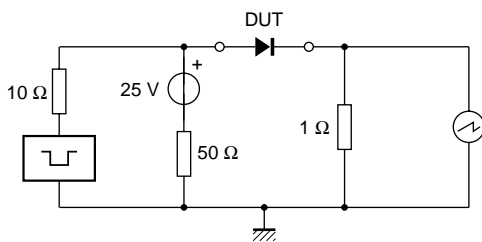
Ripple blocking diode

BYD67



Input impedance oscilloscope: 1 MΩ, 22 pF;  $t_r \leq 7$  ns.  
 Source impedance: 50 Ω;  $t_r \leq 10$  ns.

Fig.10 Test circuit and turn-on time waveform and definition.



Input impedance oscilloscope: 1 MΩ, 22 pF;  $t_r \leq 7$  ns.  
 Source impedance: 50 Ω;  $t_r \leq 15$  ns.

Fig.11 Test circuit and reverse recovery time waveform and definition.

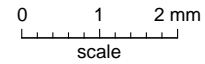
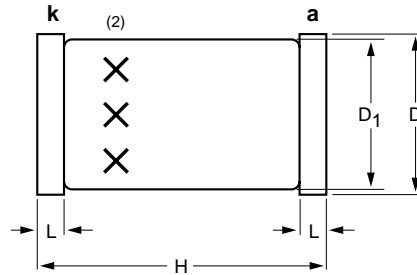
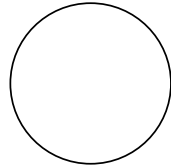
Ripple blocking diode

BYD67

PACKAGE OUTLINE

Hermetically sealed glass surface mounted package;  
Implotec™(1) technology; 2 connectors

SOD87



DIMENSIONS (mm are the original dimensions)

| UNIT | D          | D1         | H          | L   |
|------|------------|------------|------------|-----|
| mm   | 2.1<br>2.0 | 2.0<br>1.8 | 3.7<br>3.3 | 0.3 |

Notes

1. Implotec is a trademark of Philips.
2. The marking indicates the cathode.

| OUTLINE VERSION | REFERENCES |       |      |  | EUROPEAN PROJECTION | ISSUE DATE           |
|-----------------|------------|-------|------|--|---------------------|----------------------|
|                 | IEC        | JEDEC | EIAJ |  |                     |                      |
| SOD87           | 100H03     |       |      |  |                     | 99-03-31<br>99-06-04 |

## Ripple blocking diode

BYD67

## DATA SHEET STATUS

| LEVEL | DATA SHEET STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)(3)</sup> | DEFINITION   |
|-------|----------------------------------|----------------------------------|--|
| I     | Objective data                   | Development                      | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
| II    | Preliminary data                 | Qualification                    | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.             |
| III   | Product data                     | Production                       | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). |

## Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information** — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

## DISCLAIMERS

**Life support applications** — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

**Right to make changes** — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.



Ripple blocking diode

BYD67

---

**NOTES**

Ripple blocking diode

BYD67

---

**NOTES**

Ripple blocking diode

BYD67

---

**NOTES**

# ***Philips Semiconductors – a worldwide company***

## **Contact information**

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com).

© Koninklijke Philips Electronics N.V. 2003

SCA75

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613510/03/pp12

Date of release: 2003 Mar 14

Document order number: 9397 750 10977

*Let's make things better.*

**Philips  
Semiconductors**



**PHILIPS**